
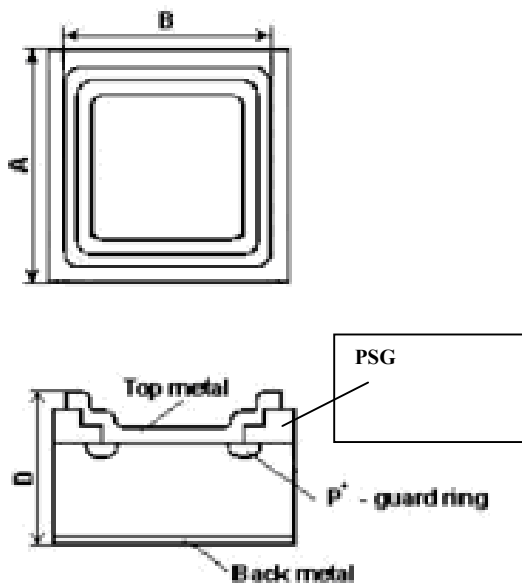


**SCHOTTKY DIODES. KDS- 08040P.**  
PRELIMINARY.



Jan. 2013.

 VSP-MIKRON	<b>8A/40V. Die Size-98mil.</b>			
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10mA$	$V_B$	V	40	45
Average Rectified Forward Current	$I_{F(AV)}$	A	8,0	-
DC Forward Voltage @ 25°C, $I_F=8,0A$	$V_F$	V	0,41	0,39
Maximum Reverse Current  @ 25°C, $V_R=45V$ 25°C, $V_R=40V$ 100°C, $V_R=40V$	$I_R$	MA	- 2,5 100,0	2,0 1,5 80,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	$I_{FSM}$	A	160	-
Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., $T_J<150°C$ .	$I_{RRM}$	A	3,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	$T_J$	°C	125	



DIM	ITEM	µm
$A_x$ $A_y$	Die Size	2500 2500
$B_x$ $B_y$	Top Metal Size	2360 2360
D	Thickness	300max.
Scribe line Width		80

*Top metal:* a) **Al** – for Wire Bonding;  
b) **Al-Ni-Ag** – for Soldering.  
*Backside metal:* **Ti-Ni-Ag**.